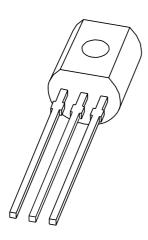
DISCRETE SEMICONDUCTORS

DATA SHEET



PSS9014CNPN general purpose transistor

Product specification Supersedes data of 2002 Mar 15 2002 Sep 20





NPN general purpose transistor

PSS9014C

FEATURES

- High power dissipation: 500 mW
- · Low collector capacitance
- Low collector-emitter saturation voltage
- · High current capability.

APPLICATIONS

• General purpose switching and amplification.

DESCRIPTION

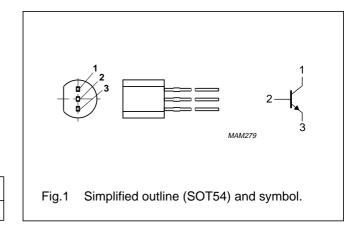
NPN low V_{CEsat} transistor in a SOT54 (TO-92) plastic package.

MARKING

TYPE NUMBER	MARKING CODE
PSS9014C	S9014C

PINNING

PIN	DESCRIPTION
1	collector
2	base
3	emitter



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	50	V
V _{CEO}	collector-emitter voltage	open base	_	45	V
V _{EBO}	emitter-base voltage	open collector	_	5	V
I _C	collector current (DC)		_	100	mA
I _{CM}	peak collector current		_	200	mA
I _{BM}	peak base current		_	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	500	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to	in free air; note 1	250	K/W
	ambient			

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 30 V; I _E = 0	_	_	15	nA
		V _{CB} = 30 V; I _E = 0; T _{amb} = 150 °C	_	_	5	μΑ
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0$	_	_	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0$	_	_	100	nA
h _{FE}	DC current gain	I _C = 1 mA; V _{CE} = 5 V	200	300	600	
		I _C = 2 mA; V _{CE} = 5 V	200	300	450	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}; \text{ note 1}$	_	200	300	mV
V _{BEsat}	base-emitter saturation voltage	$I_C = 100 \text{ mA}$; $I_B = 0.5 \text{ mA}$; note 1	_	815	850	mV
V _{BEon}	base-emitter turn-on voltage	I _C = 2 mA; V _{CE} = 5 V	580	650	700	mV
f _T	transition frequency	I _C = 50 mA; V _{CE} = 10 V; f = 100 MHz	100	220	_	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0; f = 1 \text{ MHz}$	_	1.6	1.75	pF
F	noise figure	$V_{CE} = 5 \text{ V; } I_{C} = 0.2 \text{ mA;}$ $R_{S} = 2 \text{ k}\Omega; f = 1 \text{ kHz; } B = 200 \text{ Hz}$	_	_	10	dB

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

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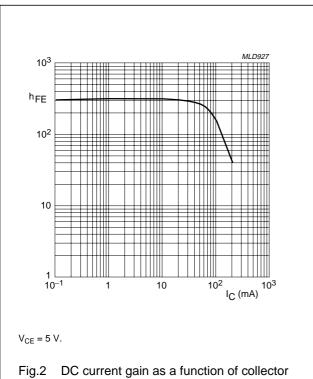


Fig.2 DC current gain as a function of collecto current; typical values.

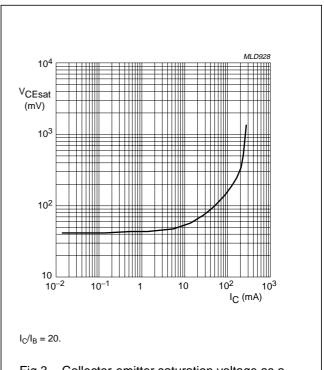
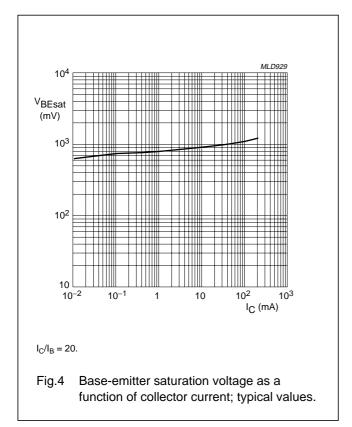
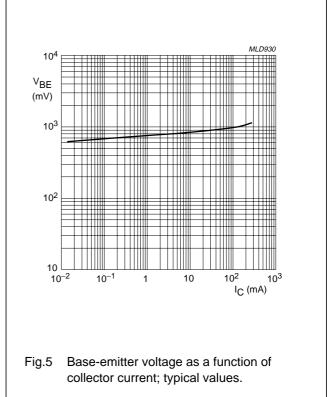


Fig.3 Collector-emitter saturation voltage as a function of collector current; typical values.





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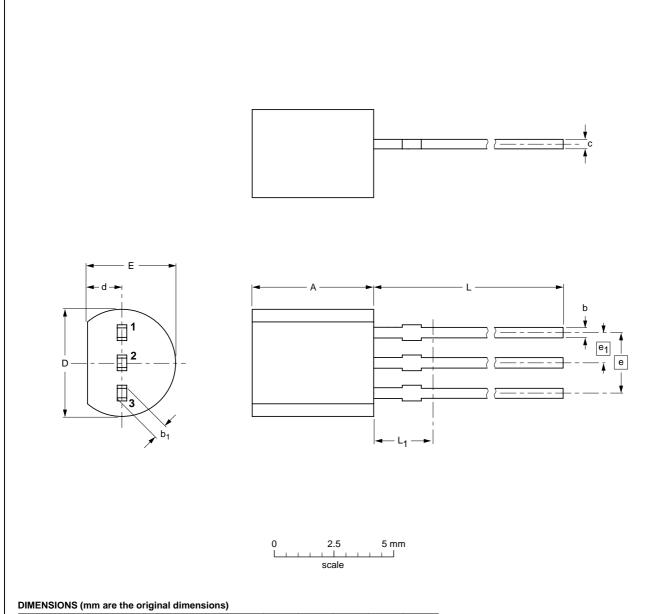
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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	Α	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFERENCES EUROPEAN ISSUE				ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	
SOT54		TO-92	SC-43			97-02-28

NPN general purpose transistor

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DATA SHEET STATUS

DATA SHEET STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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